

isc N-Channel MOSFET Transistor

1N65

• FEATURES

- Drain Current $I_D = 1.2A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 650V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 12.5 \Omega (\text{Max})$
- Fast Switching

• APPLICATIONS

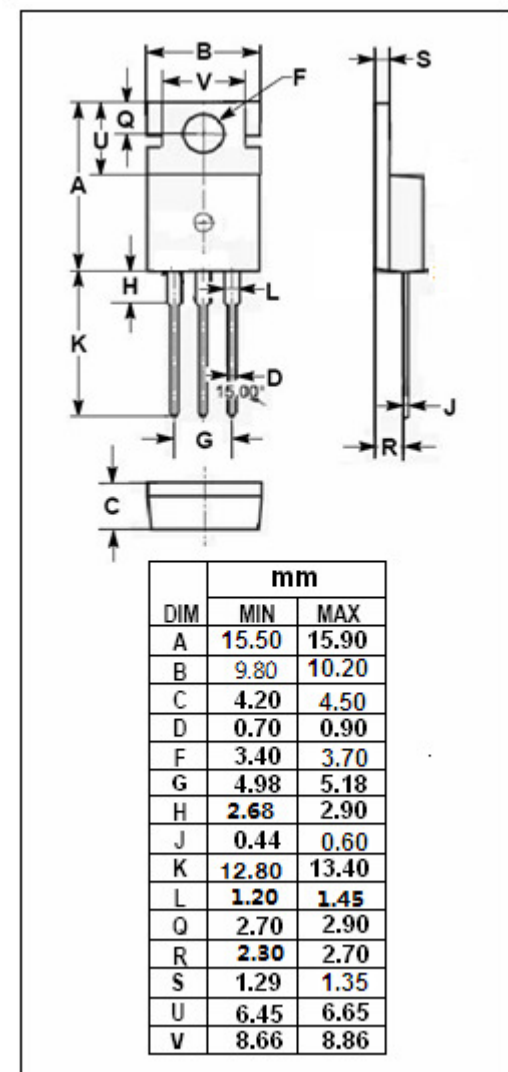
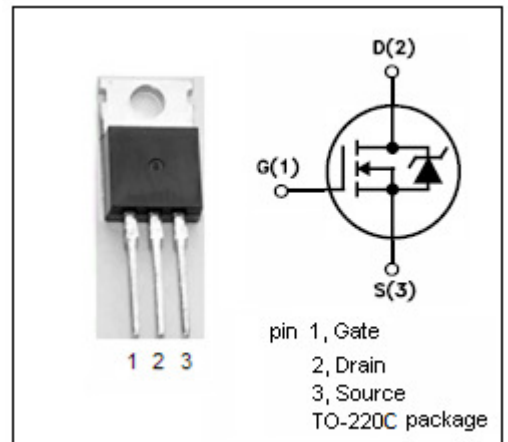
- Switching power supplies, converters, AC and DC motor controls

• ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage-Continuous	± 30	V
I_D	Drain Current-Continuous	1.2	A
I_{DM}	Drain Current-Single Plused	4.8	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	40	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	3.13	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$



isc N-Channel MOSFET Transistor**1N65****• ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=250\mu\text{A}$	650			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	2.0		4.0	V
V_{SD}	Diode Forward On-voltage	$I_S=1.2\text{A}; V_{GS}=0$			1.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=0.6\text{A}$			12.5	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650\text{V}; V_{GS}=0$			10	μA